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January 2010

## **NDS9948**

## **Dual 60V P-Channel PowerTrench® MOSFET**

## **General Description**

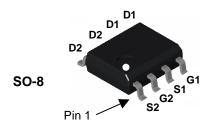
This P-Channel MOSFET is a rugged gate version of Fairchild Semiconductor's advanced PowerTrench process. It has been optimized for power management applications requiring a wide range of gate drive voltage ratings (4.5V-20V).

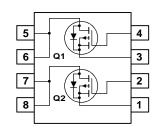
## **Applications**

- Power management
- Load switch
- Battery protection

## **Features**

- -2.3 A, -60 V  $R_{DS(ON)} = 250 \text{ m}\Omega$  @  $V_{GS} = -10 \text{ V}$   $R_{DS(ON)} = 500 \text{ m}\Omega$  @  $V_{GS} = -4.5 \text{ V}$
- Low gate charge (9nC typical)
- · Fast switching speed
- $\bullet~$  High performance trench technology for extremely low  $R_{\text{DS(ON)}}$
- High power and current handling capability





## Absolute Maximum Ratings T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V <sub>DSS</sub>	Drain-Source Voltage		-60	V
V <sub>GSS</sub>	Gate-Source Voltage		±20	V
I <sub>D</sub>	Drain Current - Continuous	(Note 1a)	-2.3	А
	– Pulsed		-10	
P <sub>D</sub>	Power Dissipation for Dual Operation		2	W
	Power Dissipation for Single Operation	(Note 1a)	1.6	
		(Note 1b)	1.0	
		(Note 1c)	0.9	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Tempera	ture Range	-55 to +175	°C

## **Thermal Characteristics**

R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient	(Note 1a)	78	°C/W
		(Note 1c)	135	°C/W
R <sub>eJC</sub>	Thermal Resistance, Junction-to-Case	(Note 1)	40	°C/W

**Package Marking and Ordering Information** 

Device Marking	Device	Reel Size	Tape width	Quantity
NDS9948	NDS9948	13"	12mm	2500 units

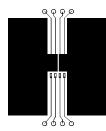
Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Drain-Sc	ource Avalanche Ratings (Note	e 2)			I	I
W <sub>DSS</sub>	Drain-Source Avalanche Energy	Single Pulse, V <sub>DD</sub> =–54 V			15	mJ
I <sub>AR</sub>	Drain-Source Avalanche Current				-10	Α
Off Char	acteristics			•	•	•
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, \qquad I_{D} = -250 \mu\text{A}$	-60			V
ΔBV <sub>DSS</sub> ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	$I_D = -250 \mu\text{A}$ , Referenced to $25^{\circ}\text{C}$		-52		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	$V_{DS} = -40 \text{ V}, V_{GS} = 0 \text{ V}$ $V_{DS} = -40 \text{ V}, V_{GS} = 0 \text{ V}$ T <sub>J</sub> =-55°C			-2 -25	μΑ
$I_{GSSF}$	Gate-Body Leakage, Forward	$V_{GS} = 20 \text{ V}, \qquad V_{DS} = 0 \text{ V}$			100	nA
$I_{GSSR}$	Gate-Body Leakage, Reverse	$V_{GS} = -20 \text{ V}$ $V_{DS} = 0 \text{ V}$			-100	nA
On Char	acteristics (Note 2)					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	-1	-1.5	-3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250 \mu A$ , Referenced to $25^{\circ}C$		4		mV/°C
$R_{DS(on)}$	Static Drain–Source On–Resistance	$V_{GS} = -10 \text{ V}, \qquad I_D = -2.3 \text{ A}$ $V_{GS} = -4.5 \text{ V}, \qquad I_D = -1.6 \text{ A}$		138 175 225	250 500 433	mΩ
I <sub>D(on)</sub>	On–State Drain Current	$V_{GS} = -10 \text{ V}, I_D = -2.3 \text{A}, T_J = 125^{\circ}\text{C}$ $V_{GS} = -10 \text{ V}, V_{DS} = -5 \text{ V}$	-10	223	433	Α
9FS	Forward Transconductance	$V_{DS} = -10 \text{ V}, \qquad I_{D} = -2.3 \text{ A}$		5		S
_	Characteristics	, , ,	<u> </u>			I
C <sub>iss</sub>	Input Capacitance	$V_{DS} = -30 \text{ V},  V_{GS} = 0 \text{ V},$		394		pF
Coss	Output Capacitance	f = 1.0 MHz		53		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			23		pF
Switchir	ng Characteristics (Note 2)		l.	I	I	I.
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD} = -30 \text{ V},  I_{D} = -1 \text{ A},$		6	12	ns
t <sub>r</sub>	Turn-On Rise Time	$V_{GS} = -10 \text{ V},  R_{GEN} = 6 \Omega$		9	18	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			16	29	ns
t <sub>f</sub>	Turn-Off Fall Time	1		3	6	ns
Qg	Total Gate Charge	$V_{DS} = -30 \text{ V}, \qquad I_{D} = -2.3 \text{ A},$		9	13	nC
Q <sub>gs</sub>	Gate-Source Charge	$V_{GS} = -10 \text{ V}$		1.4		nC
$Q_{gd}$	Gate-Drain Charge			1.7		nC

## Electrical Characteristics (cont.)<sub>T<sub>A</sub></sub> = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Drain-S	ource Diode Characteristics	and Maximum Ratings				
Is	Maximum Continuous Drain-Source Diode Forward Current				-1.7	Α
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, \qquad I_{S} = -1.7 \text{ A(Note 2)}$		-0.8	-1.2	V
t <sub>rr</sub>	Reverse Recovery Time	$V_{GS} = 0 \text{ V}, \qquad I_F = -2.3\text{A}, \\ dI_F/dt = 100\text{A}/\mu\text{s}$		25		nS

#### Notes:

 R<sub>8JA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>8JC</sub> is guaranteed by design while R<sub>8CA</sub> is determined by the user's board design.



a) 78°C/W when mounted on a 0.5in<sup>2</sup> pad of 2 oz copper



125°C/W when mounted on a 0.02 in<sup>2</sup> pad of 2 oz copper



135°C/W when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < 300 $\mu$ s, Duty Cycle < 2.0%

## **Typical Characteristics**

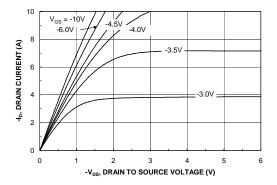


Figure 1. On-Region Characteristics.

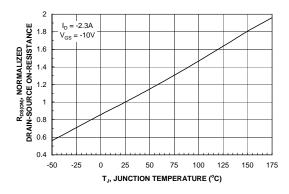


Figure 3. On-Resistance Variation withTemperature.

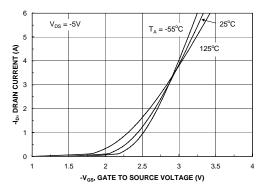


Figure 5. Transfer Characteristics.

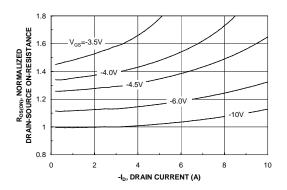


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

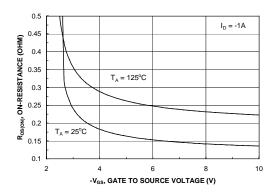


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

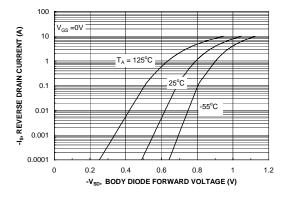
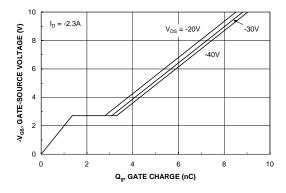


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

## **Typical Characteristics**



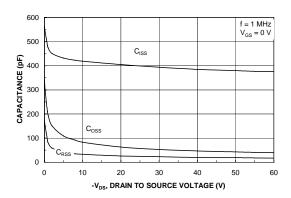
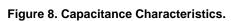
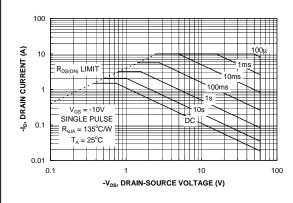


Figure 7. Gate Charge Characteristics.





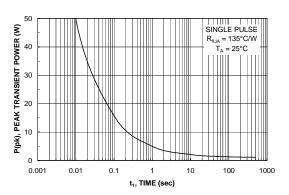


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

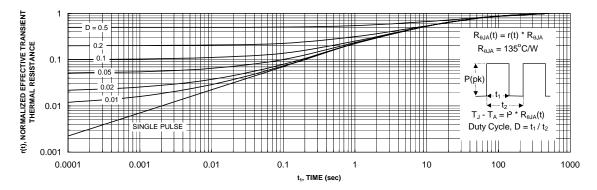


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.



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